

isc Silicon PNP Power Transistor

2SB695

DESCRIPTION

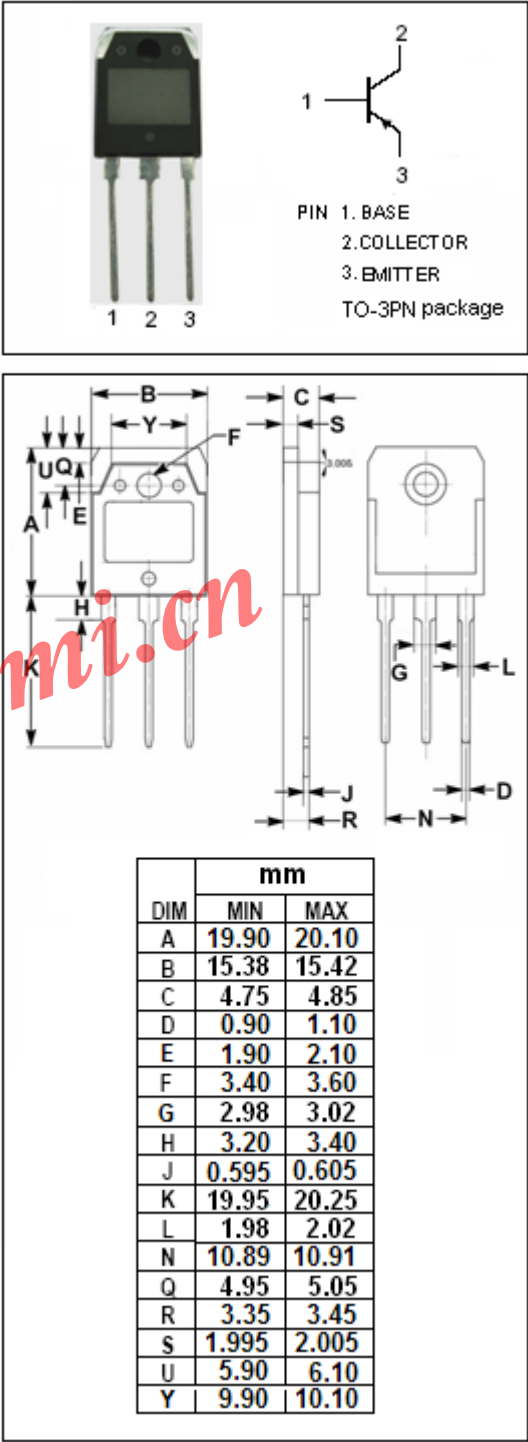
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SD731

APPLICATIONS

- Designed for power amplifier and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-170	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	80	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon PNP Power Transistor**2SB695****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}; I_E = 0$	-170			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-1.5	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -5\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -170\text{V}; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	40		200	
h_{FE-2}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -5\text{V}$	20			
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1.0\text{MHz}$		350		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		7		MHz